

HIGH CURRENT NPN SILICON TRANSISTOR

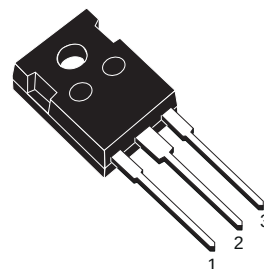
- SGS-THOMSON PREFERRED SALESTYPE
- NPN TRANSISTOR

APPLICATIONS:

- MOTOR CONTROL
- HIGH FREQUENCY AND EFFICIENCY CONVERTERS

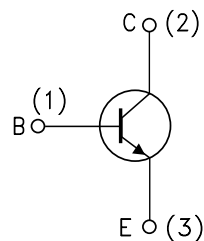
DESCRIPTION

High current, high speed transistor suited for power conversion applications, high efficiency converters and motor controls.



TO-247

INTERNAL SCHEMATIC DIAGRAM



SC06960

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CES}	Collector-Emitter Voltage ($V_{BE} = 0$)	500	V
V_{CEO}	Collector-Emitter Voltage ($I_B = 0$)	250	V
V_{EBO}	Emitter-Base Voltage ($I_C = 0$)	7	V
I_E	Emitter-Current	60	A
I_{EM}	Emitter Peak Current ($t_p < 5ms$)	70	A
I_B	Base Current	15	A
I_{BM}	Base Peak Current ($t_p < 5ms$)	18	A
P_{tot}	Total Dissipation at $T_c \leq 25^\circ C$	180	W
T_{stg}	Storage Temperature	-65 to 150	$^\circ C$
T_j	Max. Operating Junction Temperature	150	$^\circ C$

For PNP type voltage and current values are negative.

THERMAL DATA

R _{thj-case}	Thermal Resistance Junction-case	MAX	0.7	°C/W
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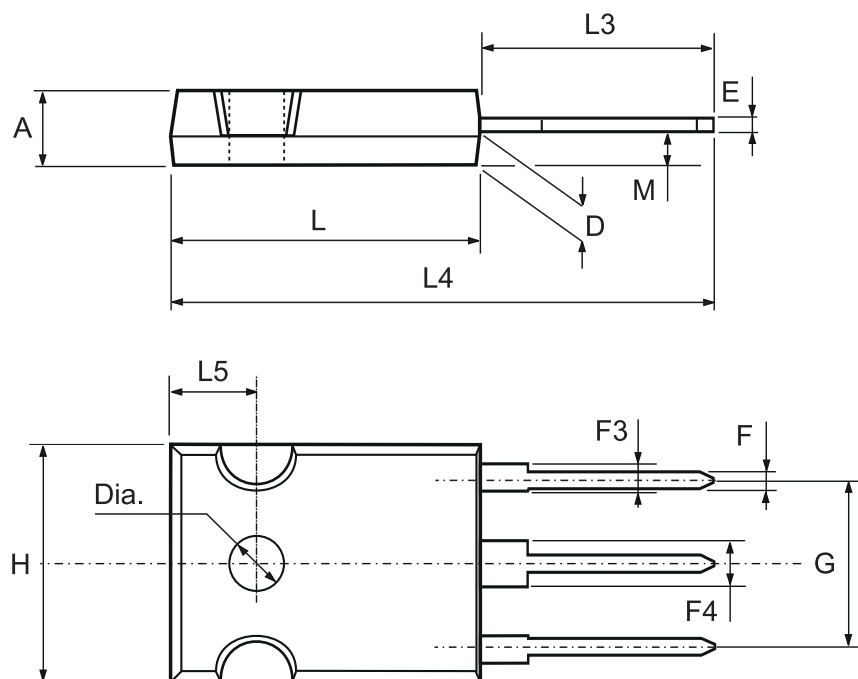
ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I _{CES}	Collector Cut-off Current (V _{BE} = -1.5V)	V _{CE} = 450 V V _{CE} = 450 V T _C = 100°C			50 1	μA mA
I _{EBO}	Emitter Cut-off Current (I _C = 0)	V _{EB} = 5 V			50	μA
V _{CES}	Collector-Emitter Breakdown Voltage (V _{EB} = 0)	I _C = 5 mA	500			V
V _{EBO}	Emitter-Base Breakdown Voltage (I _C = 0)	I _E = 50 mA	7			V
V _{CEO(sus)} *	Collector-Emitter Sustaining Voltage (I _B = 0)	I _C = 200 mA	250			V
V _{CE(sat)} *	Collector-Emitter Saturation Voltage	I _C = 60 A I _B = 15 A I _C = 60 A I _B = 15 A T _C = 100°C		0.8 1.1	1 1.5	V V
V _{BE(sat)} *	Base-Emitter Saturation Voltage	I _C = 60 A I _B = 15 A I _C = 60 A I _B = 15 A T _C = 100°C			1.9 2	V V
h _{FE} *	DC Current Gain	I _C = 60 A V _{CE} = 3 V I _C = 60 A V _{CE} = 3 V T _C = 100°C I _C = 5 A V _{CE} = 3 V	9 6		65	
t _s t _f	RESISTIVE LOAD Storage Time Fall Time	I _C = 50 A V _{CC} = 250 V I _{B1} = -I _{B2} = 10 A		1.2 250	1.4 300	μs ns

* Pulsed: Pulse duration = 300 μs, duty cycle 1.5 %

TO-247 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.7		5.3	0.185		0.209
D	2.2		2.6	0.087		0.102
E	0.4		0.8	0.016		0.031
F	1		1.4	0.039		0.055
F3	2		2.4	0.079		0.094
F4	3		3.4	0.118		0.134
G		10.9			0.429	
H	15.3		15.9	0.602		0.626
L	19.7		20.3	0.776		0.779
L3	14.2		14.8	0.559	0.413	0.582
L4		34.6			1.362	
L5		5.5			0.217	
M	2		3	0.079		0.118
Dia	3.55		3.65	0.140		0.144



P025P

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